NSN 5962-01-365-1426

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-01-365-1426

Mandanian Barras Disabatian Bathan
Maximum Power Dissipation Rating:
2.0 watts
Operating Tempurature Range:
-55.0/+125.0 degrees celsius
Storage Tempurature Range:
-65.0/+150.0 degrees celsius
End Application:
Scadc e/i fscm k0656
Features Provided:
Programmed
Inclosure Material:
Ceramic
Inclosure Configuration:
Dual-in-line
Output Logic Form:
Bipolar metal-oxide semiconductor
Input Circuit Pattern:
16 input
Case Outline Source And Designator:
D-8 mil-m-38510
Current Rating Per Characteristic:
100.00 milliamperes reverse current, dc
Terminal Surface Treatment:
Solder
Product Name:
16-input 8-output and-or invert gate array
Voltage Rating And Type Per Characteristic:
-1.5 volts absolute input and 12.0 volts absolute input
Memory Device Type:
Pal
Hybrid Technology Type:
Monolithic
Test Data Document:
K0656-9986-ccrq drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing,
etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
20 printed circuit
Specification Data:
81349-mil-m-38510 government specification and 96906-mil-std-883 government standard
Shelf Life:
N/a
Unit Of Measure:

__

NSN 5962-01-365-1426

Memory Microcircuit - Page 2 of 2



Demilitarization:

Yes - demil/mli

Fiig:

A458a0